

N-channel 40 V 2.2 mΩ standard level MOSFET in D2PAK Rev. 1 — 20 March 2012 Product data

Product data sheet

#### **Product profile** 1.

#### **1.1 General description**

Standard level N-channel MOSFET in SOT404 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

#### **1.3 Applications**

- DC-to-DC convertors
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	<u>[1]</u>	-	-	100	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	306	W
Tj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
$R_{DSon}$	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; see <u>Figure 6</u>		-	2.73	3.2	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 6</u> ; see <u>Figure 13</u>		-	1.88	2.2	mΩ
Dynamic	characteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 20 V;		-	25	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14; see Figure 15		-	130	-	nC
	e ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V; } T_{j(\text{init})} = 25 \ ^{\circ}\text{C;} \\ I_{D} = 100 \text{ A; } V_{sup} \leq 40 \text{ V; unclamped;} \\ R_{GS} = 50 \ \Omega \end{array} $		-	-	1.24	J

[1] Continuous current is limited by package

## nexperia

#### N-channel 40 V 2.2 m $\Omega$ standard level MOSFET in D2PAK

#### 2. Pinning information

Table 2.	Pinning	information				
Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	G	gate		_		
2	D	drain <sup>[1]</sup>	mb	B		
3	S	source				
mb	D	drain		mbb076 S		
			SOT404 (D2PAK)			

[1] It is not possible to make connection to pin 2

## 3. Ordering information

# Table 3. Ordering information Type number Package Name Description Version PSMN2R2-40BS D2PAK plastic single-ended surface-mounted package (D2PAK); 3 leads SOT404 (one lead cropped)

#### 4. Marking

Table 4.   Marking codes	
Type number	Marking code
PSMN2R2-40BS	PSMN2R2-40BS

#### N-channel 40 V 2.2 m $\Omega$ standard level MOSFET in D2PAK

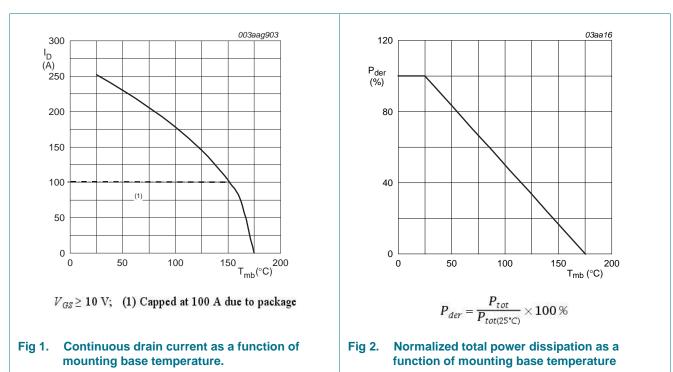
## 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

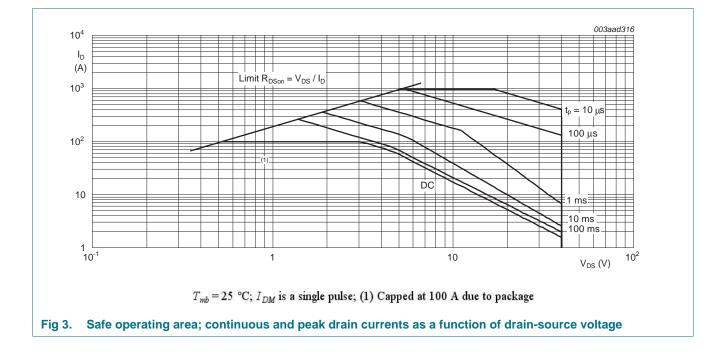
Parameter	Conditions		Min	Max	Unit
drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ		-	40	V
gate-source voltage			-20	20	V
drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	[1]	-	100	А
	$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	[1]	-	100	А
peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3		-	962	А
total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	306	W
storage temperature			-55	175	°C
junction temperature			-55	175	°C
peak soldering temperature			-	260	°C
ain diode					
source current	T <sub>mb</sub> = 25 °C	[1]	-	100	А
peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	962	А
ruggedness					
non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le 40$ V; unclamped; $R_{GS}$ = 50 $\Omega$		-	1.24	J
	drain-source voltage drain-gate voltage gate-source voltage drain current peak drain current total power dissipation storage temperature junction temperature peak soldering temperature ain diode source current peak source current ruggedness non-repetitive drain-source	$\begin{array}{ll} drain-source \ voltage & T_j \geq 25 \ ^{\circ}\text{C}; \ T_j \leq 175 \ ^{\circ}\text{C} \\ drain-gate \ voltage & T_j \geq 25 \ ^{\circ}\text{C}; \ T_j \leq 175 \ ^{\circ}\text{C}; \ R_{GS} = 20 \ \text{k}\Omega \\ gate-source \ voltage & & & & \\ \\ drain \ current & V_{GS} = 10 \ ^{\vee}\text{V}; \ T_{mb} = 100 \ ^{\circ}\text{C}; \ see \ Figure 1 \\ \hline V_{GS} = 10 \ ^{\vee}\text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ see \ Figure 1 \\ \hline v_{GS} = 10 \ ^{\vee}\text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ see \ Figure 2 \\ total \ power \ dissipation & T_{mb} = 25 \ ^{\circ}\text{C}; \ see \ Figure 2 \\ storage \ temperature & & \\ junction \ temperature & & \\ peak \ soldering \ temperature & & \\ peak \ soldering \ temperature & & \\ \hline non \ repetitive \ drain-source & V_{GS} = 10 \ ^{\vee}\text{V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \ I_D = 100 \ ^{\vee}\text{A}; \end{array}$	$\label{eq:rescaled} \begin{array}{ll} T_{j} \geq 25 \ ^{\circ}\text{C}; \ T_{j} \leq 175 \ ^{\circ}\text{C} \\ \\ \text{drain-gate voltage} \\ \\ \text{drain-gate voltage} \\ \\ \text{drain current} \\ \begin{array}{ll} V_{GS} = 10 \ ^{\circ}\text{V}; \ T_{mb} = 100 \ ^{\circ}\text{C}; \ \text{see Figure 1} \\ \\ V_{GS} = 10 \ ^{\circ}\text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 1} \\ \\ V_{GS} = 10 \ ^{\circ}\text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 1} \\ \end{array} \begin{array}{ll} \begin{array}{ll} 11 \\ \\ Peak \ drain \ current \\ pulsed; \ t_{p} \leq 10 \ ^{\circ}\text{y}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 3} \\ \\ \text{total power dissipation} \\ \\ \text{total power dissipation} \\ T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 2} \\ \\ \text{storage temperature} \\ \\ \\ peak \ \text{soldering temperature} \\ \\ \\ \hline \text{peak soldering temperature} \\ \\ \hline \text{source current} \\ \\ \\ T_{mb} = 25 \ ^{\circ}\text{C} \\ \\ \hline T_{mb} = 25 \ ^{\circ}\text{C} \\ \\ \hline \text{ruggedness} \\ \\ \\ \text{non-repetitive drain-source} \\ \end{array} \begin{array}{ll} V_{GS} = 10 \ ^{\circ}\text{V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \ ^{1}\text{b} = 100 \ ^{\circ}\text{A}; \\ \end{array}$	$\begin{array}{cccc} drain-source voltage & T_j \geq 25 \ ^{\circ}\text{C}; \ T_j \leq 175 \ ^{\circ}\text{C} & - & \\ drain-gate voltage & T_j \geq 25 \ ^{\circ}\text{C}; \ T_j \leq 175 \ ^{\circ}\text{C}; \ R_{GS} = 20 \ \text{k}\Omega & - & \\ gate-source voltage & -20 \\ drain current & & V_{GS} = 10 \ \text{V}; \ T_{mb} = 100 \ ^{\circ}\text{C}; \ \text{see Figure 1} & [1] & - & \\ & V_{GS} = 10 \ \text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 1} & [1] & - & \\ & V_{GS} = 10 \ \text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 3} & - & \\ total power dissipation & T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 2} & - & \\ storage temperature & & & -55 \\ junction temperature & & & -55 \\ peak soldering temperature & & & -55 \\ peak soldering temperature & & & & - & \\ \hline \textbf{not diode} & & & \\ source current & T_{mb} = 25 \ ^{\circ}\text{C} & & [1] & - & \\ pulsed; \ t_p \leq 10 \ \text{\mu}s; \ T_{mb} = 25 \ ^{\circ}\text{C} & & & [1] & - & \\ peak source current & pulsed; \ t_p \leq 10 \ \text{\mu}s; \ T_{mb} = 25 \ ^{\circ}\text{C} & & \\ \hline \textbf{non-repetitive drain-source} & V_{GS} = 10 \ \text{V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \ I_D = 100 \ \text{A}; & - & \\ \end{array}$	$\begin{array}{cccc} drain-source voltage & T_j \ge 25 \ ^{\circ}\text{C}; \ T_j \le 175 \ ^{\circ}\text{C} & - & 40 \\ \\ drain-gate voltage & T_j \ge 25 \ ^{\circ}\text{C}; \ T_j \le 175 \ ^{\circ}\text{C}; \ R_{GS} = 20 \ \text{k}\Omega & - & 40 \\ \\ gate-source voltage & -20 & 20 \\ \\ drain current & V_{GS} = 10 \ \text{V}; \ T_{mb} = 100 \ ^{\circ}\text{C}; \ \text{see Figure 1} & 11 & - & 100 \\ \hline V_{GS} = 10 \ \text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 1} & 11 & - & 100 \\ \hline V_{GS} = 10 \ \text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 3} & - & 962 \\ total power dissipation & T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 2} & - & 306 \\ \text{storage temperature} & -55 & 175 \\ \text{junction temperature} & -55 & 175 \\ \text{peak soldering temperature} & -55 & 175 \\ \text{peak soldering temperature} & -55 & 175 \\ \text{source current} & T_{mb} = 25 \ ^{\circ}\text{C} & 10 \ \text{µs}; \ T_{mb} = 25 \ ^{\circ}\text{C} & - & 260 \\ \hline \textbf{ain diode} & & & & & & & & \\ \hline \textbf{ruggedness} & & & & & & & & & & \\ non-repetitive drain-source & V_{GS} = 10 \ \text{V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \ \text{I}_{D} = 100 \ \text{A}; & & & & & & & & & & & & & & & & & & &$

[1] Continuous current is limited by package



## PSMN2R2-40BS

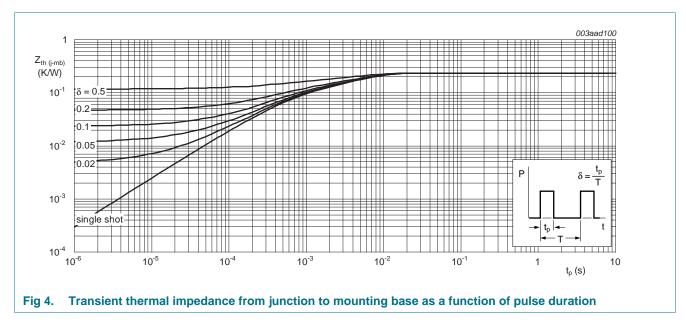
#### N-channel 40 V 2.2 mΩ standard level MOSFET in D2PAK



#### N-channel 40 V 2.2 mΩ standard level MOSFET in D2PAK

#### **Thermal characteristics** 6.

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 4	-	0.25	0.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum foot print; mounted in a printed circuit board	-	50	-	K/W



#### Table 6 Thermal characteristics

N-channel 40 V 2.2 m $\Omega$  standard level MOSFET in D2PAK

## 7. Characteristics

#### Table 7. Characteristics

Tested to JEDEC standards where applicable.

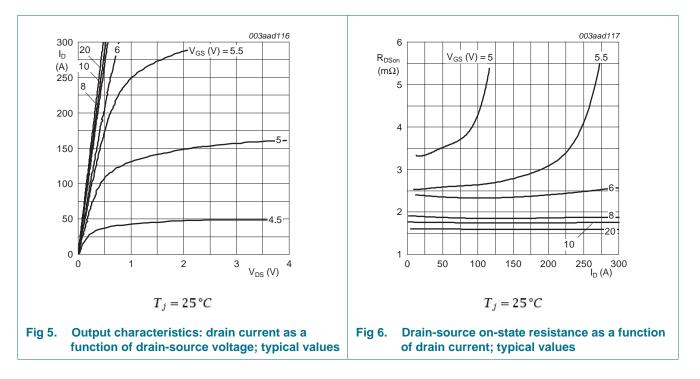
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V <sub>(BR)DSS</sub> drain-source breakdown voltage		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	36	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	40	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 11</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 11	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 11</u>	2	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.02	10	μΑ
		$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 125 °C	-	-	200	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
		$V_{GS} = -20 \text{ V};  V_{DS} = 0 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 6	-	2.73	3.2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see Figure 13; see Figure 6	-	3.76	4.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 6</u> ; see <u>Figure 13</u>	-	1.88	2.2	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic c	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}$	-	110	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V};$	-	130	-	nC
$Q_{GS}$	gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	42	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	24	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	18	-	nC
$Q_{GD}$	gate-drain charge		-	25	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 20 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	4.95	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	8423	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	1671	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	814	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 20 \text{ V}; \text{ R}_{L} = 0.25 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	33.2	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 1.5 \Omega$	-	40.4	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	66.6	-	ns
t <sub>f</sub>	fall time		-	25.2	-	ns

#### N-channel 40 V 2.2 m $\Omega$ standard level MOSFET in D2PAK

#### Table 7. Characteristics ...continued

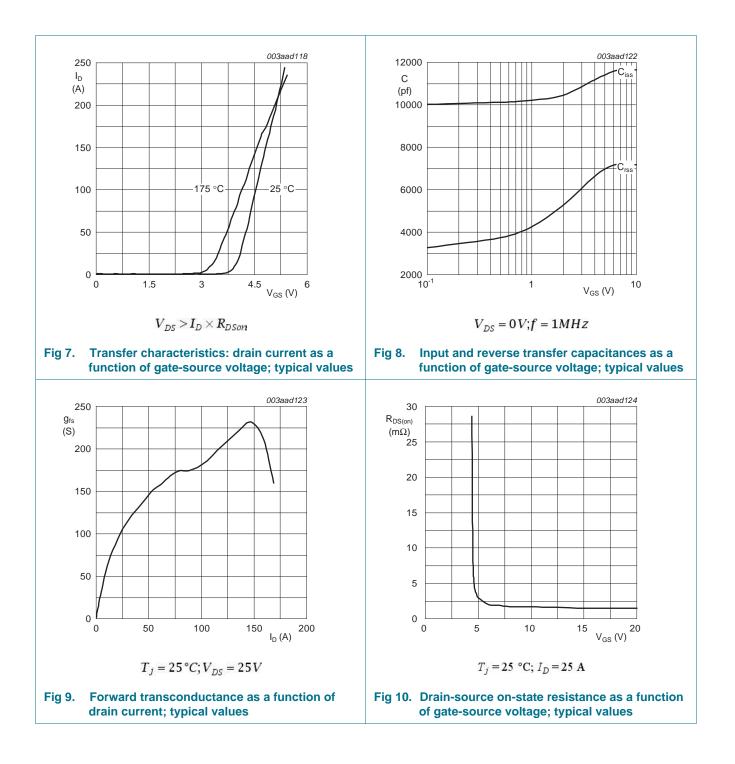
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Source-dra	ain diode					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 20 V	-	53.7	-	ns
Qr	recovered charge	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C	-	80.75	-	nC



## PSMN2R2-40BS

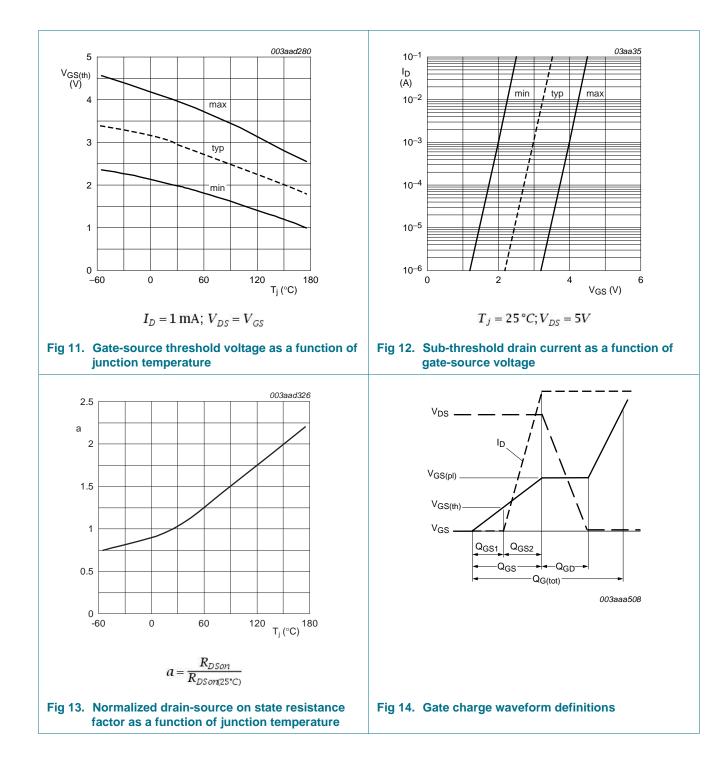
#### N-channel 40 V 2.2 mΩ standard level MOSFET in D2PAK



PSMN2R2-40BS

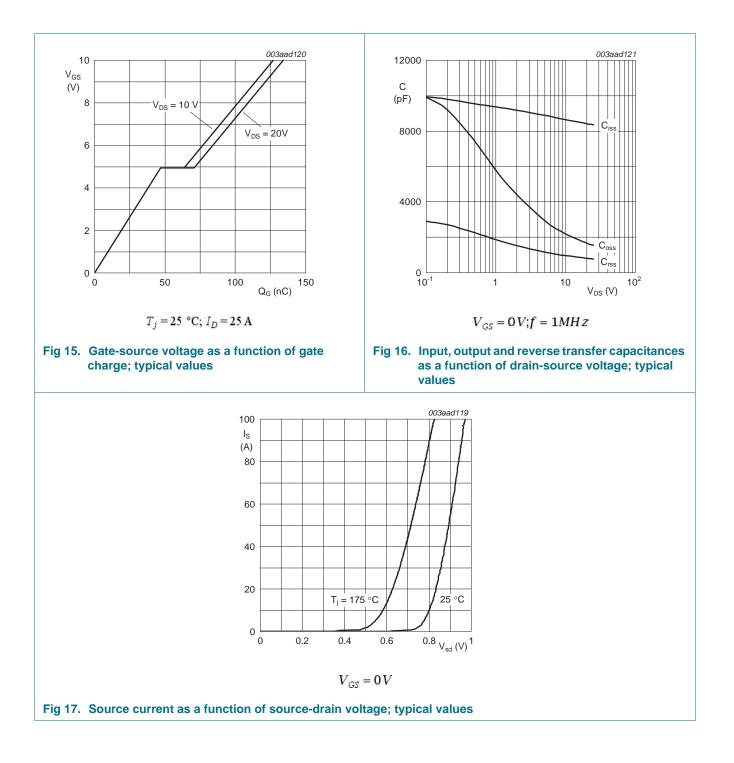
## PSMN2R2-40BS

#### N-channel 40 V 2.2 m $\Omega$ standard level MOSFET in D2PAK



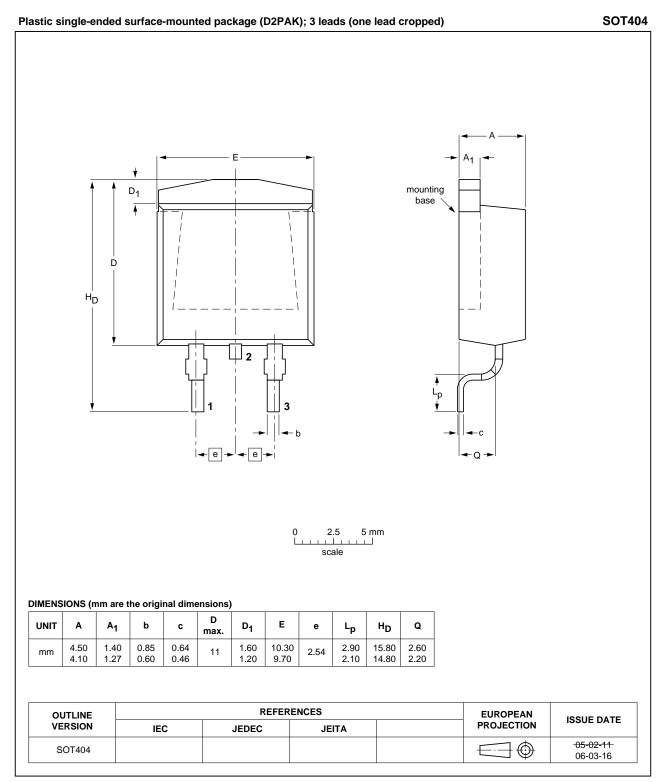
## PSMN2R2-40BS

#### N-channel 40 V 2.2 m $\Omega$ standard level MOSFET in D2PAK



#### N-channel 40 V 2.2 m $\Omega$ standard level MOSFET in D2PAK

#### 8. Package outline



#### Fig 18. Package outline SOT404 (D2PAK)

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PSMN2R2-40BS

#### N-channel 40 V 2.2 mΩ standard level MOSFET in D2PAK

## 9. Revision history

Table 8. Revision h	Revision history							
Document ID	Release date	Data sheet status	Change notice	Supersedes				
PSMN2R2-40BS v.1	20120320	Product data sheet	-	-				

#### **10. Legal information**

#### **10.1 Data sheet status**

Document status[1] [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Product data sheet

PSMN2R2-40BS

#### N-channel 40 V 2.2 m $\Omega$ standard level MOSFET in D2PAK

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#### N-channel 40 V 2.2 m $\Omega$ standard level MOSFET in D2PAK

#### 12. Contents

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